



NPN 2N6253 – 2N6254 – 2N6371

HIGH POWER SILICON NPN TRANSISTORS

The 2N6253, 2N6254, and 2N6371 are silicon transistors are mounted in TO-3 metal package.

They are intended for a wide variety of high-power applications. The construction of these devices renders them highly resistant to second breakdown over a wide range of operating conditions.

These devices differ in maximum ratings for voltage and power dissipation.

Compliance to RoHS.

ABSOLUTE MAXIMUM RATINGS

Symbol	Ratings		Value	Unit	
$V_{CEO(SUS)}$	Collector-Emitter Voltage	2N6253	45	V	
		2N6254	80		
		2N6371	40		
V_{CBO}	Collector-Base Voltage (*)	2N6253	55	V	
		2N6254	100		
		2N6371	50		
$V_{CER(SUS)}$	Collector-Emitter Voltage $R_{BE}=100\Omega$	2N6253	55	V	
		2N6254	85		
		2N6371	45		
$V_{CEV(SUS)}$	Collector-Emitter Voltage $V_{BE}=-1.5V$	2N6253	55	V	
		2N6254	90		
		2N6371	50		
V_{EBO}	Emitter-Base Voltage	2N6253	5	V	
		2N6254	7		
		2N6371	5		
I_C	Collector Current		15	A	
I_B	Base Current		7	A	
P_{TOT}	Power Dissipation	< 25°C	2N6253	115	Watts
			2N6254	150	
			2N6371	117	
			> 25°C		Derate Linearly to 200°C
T_J	Junction Temperature		-65 to +200	°C	
T_S	Storage Temperature				



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THERMAL CHARACTERISTICS

Symbol	Ratings	Value	Unit
R_{thJ-C}	Thermal Resistance, Junction to Case	2N6253	1.5
		2N6254	1.17
		2N6371	1.5

ELECTRICAL CHARACTERISTICS

TC=25°C unless otherwise noted

Symbol	Ratings	Test Condition(s)	Min	Typ	Max	Unit	
$V_{CE(SAT)}$	Collector-Emitter Voltage (*)	$I_C=3\text{ A}, I_B=0.3\text{ A}$	2N6253	-	-	1	V
		$I_C=15\text{ A}, I_B=5\text{ A}$		-	-	4	
		$I_C=5\text{ A}, I_B=0.5\text{ A}$	2N6254	-	-	0.5	
		$I_C=15\text{ A}, I_B=3\text{ A}$		-	-	4	
		$I_C=8\text{ A}, I_B=0.8\text{ A}$	2N6371	-	-	1.5	
		$I_C=16\text{ A}, I_B=4\text{ A}$		-	-	4	
I_{CEO}	Collector-Emitter Cutoff Current	$V_{CE}=25\text{ V}$	2N6253	-	-	1.5	mA
		$V_{CE}=60\text{ V}$	2N6254	-	-	1.0	
I_{EBO}	Emitter-Base Cutoff Current	$V_{EB}=-5\text{ V}$	2N6253	-	-	10	mA
		$V_{EB}=-7\text{ V}$	2N6254			0.5	
I_{CEX}	Collector Cutoff Current	$V_{CE}=40\text{ V}$ $V_{BE}=-1.5\text{ V}$	2N6371	-	-	10	mA
		$V_{CE}=50\text{ V}$ $V_{BE}=-1.5\text{ V}$	2N6253	-	-	10	
		$V_{CE}=100\text{ V}$ $V_{BE}=1.5\text{ V}$	2N6254	-	-	5.0	
		$V_{CE}=45\text{ V}$ $V_{BE}=-1.5\text{ V}$	2N6371	-	-	2.0	
		$V_{CE}=55\text{ V}$ $V_{BE}=-1.5\text{ V}$	2N6253	-	-	2.0	
		$V_{CE}=100\text{ V}$ $V_{BE}=1.5\text{ V}$	2N6254	-	-	0.5	

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ELECTRICAL CHARACTERISTICS

TC=25°C unless otherwise noted

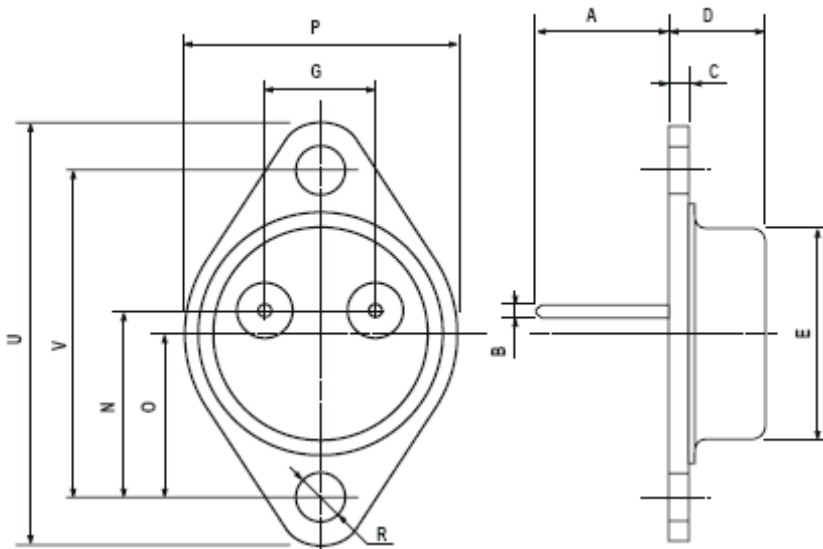
Symbol	Ratings	Test Condition(s)	Min	Typ	Max	Unit	
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage (*)	$I_C=0.2\text{ A}, I_B=0\text{ A}$	2N6253	45	-	-	V
			2N6254	80	-	-	
			2N6371	40	-	-	
$V_{CER(SUS)}$	Collector-Emitter Sustaining Voltage (*) $R_{BE}=100\Omega$	$I_C=0.2\text{ mA}$	2N6253	55	-	-	V
			2N6254	85	-	-	
			2N6371	45	-	-	
$V_{CEV(SUS)}$	Base-Emitter Voltage (*)	$I_C=0.1\text{ A}$ $V_{BE}=-1.5\text{ V}$	2N6253	55	-	-	V
			2N6254	90	-	-	
			2N6371	50	-	-	
V_{BE}	Base-Emitter Voltage (*)	$V_{CE}=4\text{ V}, I_C=3\text{ A}$	2N6253	-	-	1.7	V
		$V_{CE}=2\text{ V}, I_C=5\text{ A}$	2N6254	-	-	1.5	
		$V_{CE}=4\text{ V}, I_C=16\text{ A}$	2N6371	-	-	4	
h_{FE}	Static Forward Current transfer ratio (*)	$V_{CE}=4\text{ V}, I_C=3\text{ A}$	2N6253	20	-	70	-
		$V_{CE}=4\text{ V}, I_C=15\text{ A}$		3	-	-	
		$V_{CE}=2\text{ V}, I_C=5\text{ A}$	2N6254	20	-	70	
		$V_{CE}=4\text{ V}, I_C=15\text{ A}$		5	-	-	
		$V_{CE}=4\text{ V}, I_C=8\text{ A}$	2N6371	15	-	60	
		$V_{CE}=4\text{ V}, I_C=16\text{ A}$		4	-	-	
h_{fe}	Small Signal Current Gain	$V_{CE}=4\text{ V}, I_C=1\text{ A}$ $f=1\text{ kHz}$	2N6253	10	-	-	-
			2N6254				
			2N6371				
f_T	Transition Frequency	$V_{CE}=4\text{ V}, I_C=1\text{ A}$	2N6253	-	-	-	kHz
			2N6254	-	-	-	
			2N6371	800	-	-	
$I_{s/b}$	Second Breakdown Collector Current $t_p=1\text{ s}, \text{ non rep.}$	$V_{CE}=45\text{ V}$	2N6253	2.55	-	-	A
			2N6254	1.87	-	-	
		$V_{CE}=40\text{ V}$	2N6371	2.9	-	-	

(*) Pulse Width $\approx 300\ \mu\text{s}$, Duty Cycle $\leq 2.0\%$

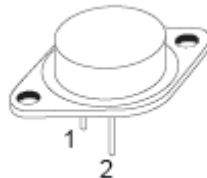
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MECHANICAL DATA CASE TO-3

DIMENSIONS (mm)			
	min	typ	max
A	11	-	13.10
B	0.97	-	1.15
C	1.5	-	1.65
D	8.32	-	8.92
E	19	-	22
G	10.70	-	11.1
N	16.50	-	17.20
P	25	-	27,20
R	3.84	-	4.21
U	38.50	-	40.13
V	29.90	-	30.40



Pin 1 :	Base
Pin 2 :	Emitter
Case :	Collector



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